Electronic supplementary information for

Geometric and electronic properties of Si-atom-doped Al clusters: Robustness of binary superatoms against charging

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(Received;

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Full citation of Ref. 60.

M. J. Frisch, G. W. Trucks, H. B. Schlegel, G. E. Scuseria, M. A. Robb, J. R. Cheeseman, G. Scalmani, V. Barone, B. Mennucci, G. A. Petersson, H. Nakatsuji, M. Caricato, X. Li, H. P. Hratchian, A. F. Izmaylov, J. Bloino, G. Zheng, J. L. Sonnenberg, M. Hada, M. Ehara, K. Toyota, R. Fukuda, J. Hasegawa, M. Ishida, T. Nakajima, Y. Honda, O. Kitao, H. Nakai, T. Vreven, J. A. Montgomery, Jr., J. E. Peralta, F. Ogliaro, M. Bearpark, J. J. Heyd, E. Brothers, K. N. Kudin, V. N. Staroverov, T. Keith, R. Kobayashi, J. Normand, K. Raghavachari, A. Rendell, J. C. Burant, S. S. Iyengar, J. Tomasi, M. Cossi, N. Rega, J. M. Millam, M. Klene, J. E. Knox, J. B. Cross, V. Bakken, C. Adamo, J. Jaramillo, R. Gomperts, R. E. Stratmann, O. Yazyev, A. J. Austin, R. Cammi, C. Pomelli, J. W. Ochterski, R. L. Martin, K. Morokuma, V. G. Zakrzewski, G. A. Voth, P. Salvador, J. J. Dannenberg, S. Dapprich, A. D. Daniels, O. Farkas, J. B. Foresman, J. V. Ortiz, J. Cioslowski and D. J. Fox, *Gaussian 09, Revision E.01*, Gaussian, Inc., Wallingford, CT, 2013.



Figure S1. Photoionization efficiency plots for Al_n clusters (n = 7, 10, 11, 12, and 14-32) with ionization energy values, where uncertainties are given in parentheses in the last digit(s).



Figure S2. Photoionization efficiency plots for Al_nSi clusters (n = 7, 9, 11, and 13–31) with ionization energy values, where uncertainties are given in parentheses in the last digit(s).



Figure S3. Photoionization efficiency plots for Al_nSi_2 clusters (n = 7 and 9–30) with ionization energy values, where uncertainties are given in parentheses in the last digit(s).



Figure S4. Optimized Geometries of (a) $Al_{10}Si^{-/0/+}$, (b) $Al_{12}Si^{-/0/+}$, and (c) $Al_{11}Si2^{-/0/+}$ with Mulliken populations.



Figure S5. Occupied and virtual frontier orbitals from HOMO - 9 to LUMO + 4 for Al₁₂Si.



Figure S6. Occupied and virtual frontier orbitals from HOMO – 9 to LUMO + 4 forAl₁₂Si⁻.



Figure S7. Occupied and virtual frontier orbitals from HOMO - 9 to LUMO + 3 for Al₁₁Si₂⁺



Figure S8. Occupied and virtual frontier orbitals from HOMO - 9 to LUMO + 3 for Al₁₁Si₂.



Figure S9. Occupied and virtual frontier orbitals from HOMO – 9 to LUMO + 4 for $Al_{11}Si_2^{-}$.



Figure S10. Occupied and virtual frontier orbitals from HOMO-9 to LUMO+4 for Al₁₂SiF⁻.



Figure S11. The relative reactivity for the cationic $Al_nSi_2^+$ clusters at n = 8-19 against O₂ molecules. Local maxima are observed at n = 11 and 17. Both $Al_{11}Si_2^+$ and $Al_{17}Si_2^+$ satisfy the SAO closings of 2P (40 *e*) and 1G (58 *e*), respectively, and the low reactivities are explicable of electronic stability.



Figure S12. Calculated energy diagram and orbital shapes of LCSAO-MOs for *bi*-icosahedral Al₂₁Si₂. Solid lines show filled or half-filled states, whereas dotted lines do unoccupied states.



Figure S12. (continued) Calculated energy diagram and orbital shapes of LCSAO-MOs for *bi*-icosahedral Al₂₁Si₂. Solid lines show filled or half-filled states, whereas dotted lines do unoccupied states.